Microchip Technology - AGLN125V5-ZCSG81 Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	3072
Total RAM Bits	36864
Number of I/O	60
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	81-WFBGA, CSBGA
Supplier Device Package	81-CSP (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agln125v5-zcsg81

Flash Advantages

Low Power

Flash-based IGLOO nano devices exhibit power characteristics similar to those of an ASIC, making them an ideal choice for power-sensitive applications. IGLOO nano devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

IGLOO nano devices also have low dynamic power consumption to further maximize power savings; power is reduced even further by the use of a 1.2 V core voltage.

Low dynamic power consumption, combined with low static power consumption and Flash*Freeze technology, gives the IGLOO nano device the lowest total system power offered by any FPGA.

Security

Nonvolatile, flash-based IGLOO nano devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. IGLOO nano devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

IGLOO nano devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of security in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in IGLOO nano devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. AES was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. IGLOO nano devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. IGLOO nano devices with AES-based security provide a high level of protection for remote field updates over public networks such as the Internet, and are designed to ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of IGLOO nano devices. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. IGLOO nano devices, with FlashLock and AES security, are unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. An IGLOO nano device provides the best available security for programmable logic designs.

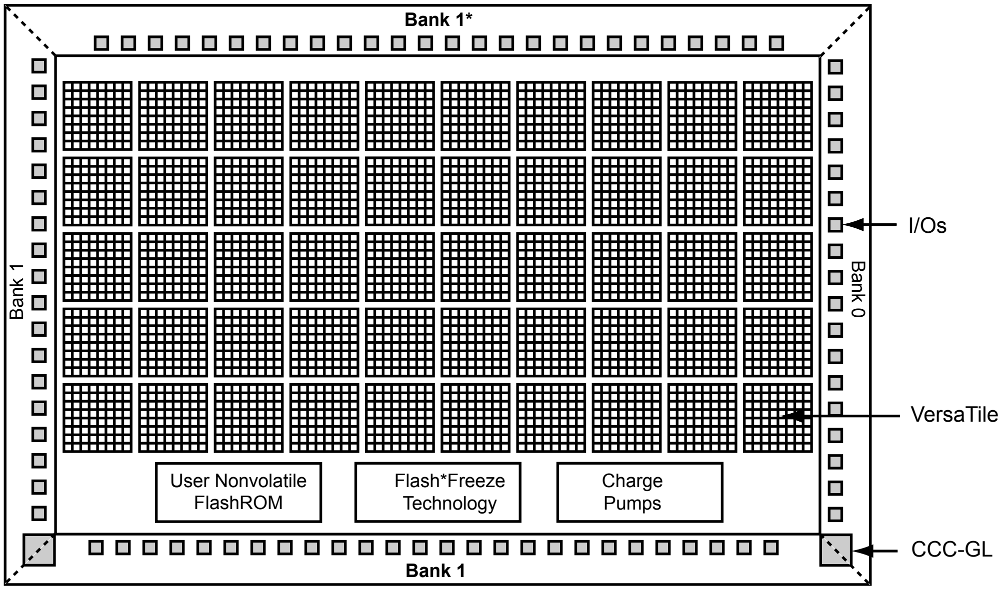
Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based IGLOO nano FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Microsemi flash-based IGLOO nano devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based IGLOO nano devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs. In addition, glitches and brownouts in system power will not corrupt the IGLOO nano device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based IGLOO nano devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

IGLOO nano flash FPGAs enable the user to quickly enter and exit Flash*Freeze mode. This is done almost instantly (within 1 µs) and the device retains configuration and data in registers and RAM. Unlike SRAM-based FPGAs, the device does not need to reload configuration and design state from external memory components; instead it retains all necessary information to resume operation immediately.



*Note: *Bank 0 for the AGLN030 device*

Figure 1-1 • **IGLOO Device Architecture Overview with Two I/O Banks and No RAM (AGLN010 and AGLN030)**

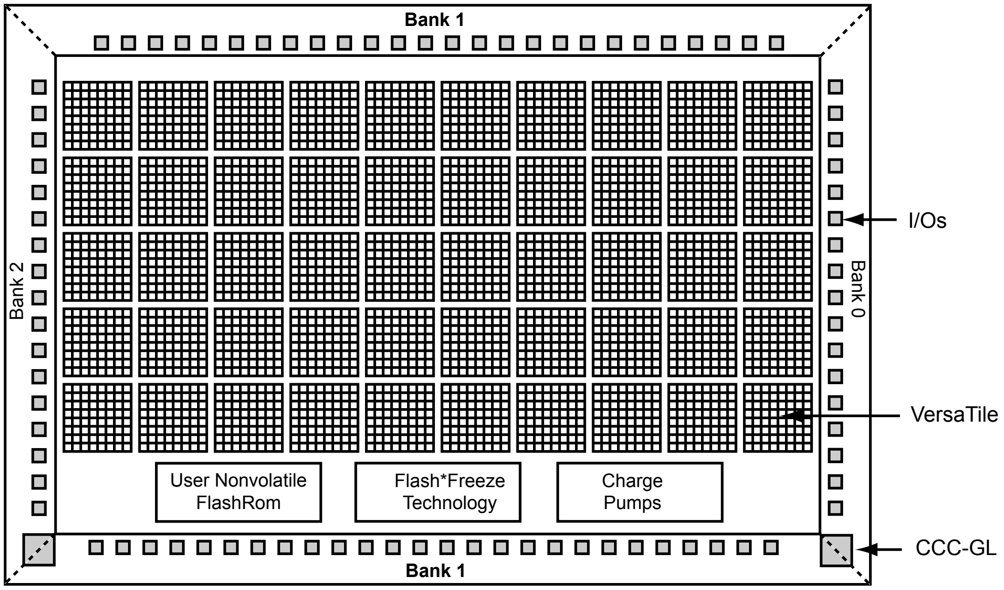


Figure 1-2 • **IGLOO Device Architecture Overview with Three I/O Banks and No RAM (AGLN015 and AGLN020)**

3.3 V LVCMOS Wide Range

Table 2-40 • **Minimum and Maximum DC Input and Output Levels for LVCMOS 3.3 V Wide Range**

3.3 V LVCMOS Wide Range[1]	Equivalent Software Default Drive Strength Option[4]	VIL		VIH		VOL	VOH	IOL	I_{OH}	IIL [2]	IIH [3]
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100	100	10	10

Notes:

1. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V Wide Range, as specified in the JEDEC JESD8-B specification.*
2. *I_{IL} is the input leakage current per I/O pin over recommended operating conditions where –0.3 < VIN < VIL.*
3. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions where VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
4. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection is highlighted in gray.*

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-41 • **3.3 V LVCMOS Wide Range Low Slew – Applies to 1.5 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V**

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	STD	0.97	5.23	0.19	1.20	1.66	0.66	5.24	5.00	2.47	2.56	ns
100 µA	4 mA	STD	0.97	5.23	0.19	1.20	1.66	0.66	5.24	5.00	2.47	2.56	ns
100 µA	6 mA	STD	0.97	4.27	0.19	1.20	1.66	0.66	4.28	4.12	2.83	3.16	ns
100 µA	8 mA	STD	0.97	4.27	0.19	1.20	1.66	0.66	4.28	4.12	2.83	3.16	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-42 • **3.3 V LVCMOS Wide Range High Slew – Applies to 1.5 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V**

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	STD	0.97	3.11	0.19	1.20	1.66	0.66	3.13	2.55	2.47	2.70	ns
100 µA	4 mA	STD	0.97	3.11	0.19	1.20	1.66	0.66	3.13	2.55	2.47	2.70	ns
100 µA	6 mA	STD	0.97	2.56	0.19	1.20	1.66	0.66	2.57	2.02	2.82	3.31	ns
100 µA	8 mA	STD	0.97	2.56	0.19	1.20	1.66	0.66	2.57	2.02	2.82	3.31	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
3. *Software default selection highlighted in gray.*

1.2 V LVCMOS (JESD8-12A)

Low-Voltage CMOS for 1.2 V complies with the LVCMOS standard JESD8-12A for general purpose 1.2 V applications. It uses a 1.2 V input buffer and a push-pull output buffer.

Table 2-63 • **Minimum and Maximum DC Input and Output Levels**

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL [1]	IIH [2]
Drive Strength	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[3]**	**Max. mA[3]**	**μA[4]**	**μA[4]**
1 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1	10	13	10	10

Notes:

1. *I_{IL} is the input leakage current per I/O pin over recommended operating conditions where –0.3 < VIN < VIL.*
2. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions where VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

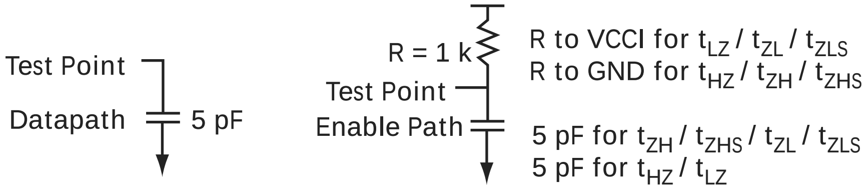


Figure 2-11 • **AC Loading**

Table 2-64 • **1.2 V LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads**

Input LOW (V)	Input HIGH (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.2	0.6	5

Note: _*Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points._

Timing Characteristics

Applies to 1.2 V DC Core Voltage

Table 2-65 • **1.2 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
1 mA	STD	1.55	8.30	0.26	1.56	2.27	1.10	7.97	7.54	2.56	2.55	ns

Note: *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-66 • **1.2 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
1 mA	STD	1.55	3.50	0.26	1.56	2.27	1.10	3.37	3.10	2.55	2.66	ns

Note: *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

1.2 V LVCMOS Wide Range

Table 2-67 • Minimum and Maximum DC Input and Output Levels

1.2 V LVCMOS Wide Range	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL [1]	IIH [2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	μA[4]	μA[4]
1 mA	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	100	100	10	13	10	10

Notes:

1. *I_{IL} is the input leakage current per I/O pin over recommended operating conditions where –0.3 < VIN < VIL.*
2. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions where VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Applicable to IGLOO nano V2 devices operating at VCCI ≥ VCC.*
6. *Software default selection highlighted in gray.*

Timing Characteristics

Applies to 1.2 V DC Core Voltage

Table 2-68 • 1.2 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	1 mA	STD	1.55	8.30	0.26	1.56	2.27	1.10	7.97	7.54	2.56	2.55	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-69 • 1.2 V LVCMOS Wide Range HIgh Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	1 mA	STD	1.55	3.50	0.26	1.56	2.27	1.10	3.37	3.10	2.55	2.66	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
3. *Software default selection highlighted in gray.*

Fully Registered I/O Buffers with Asynchronous Clear

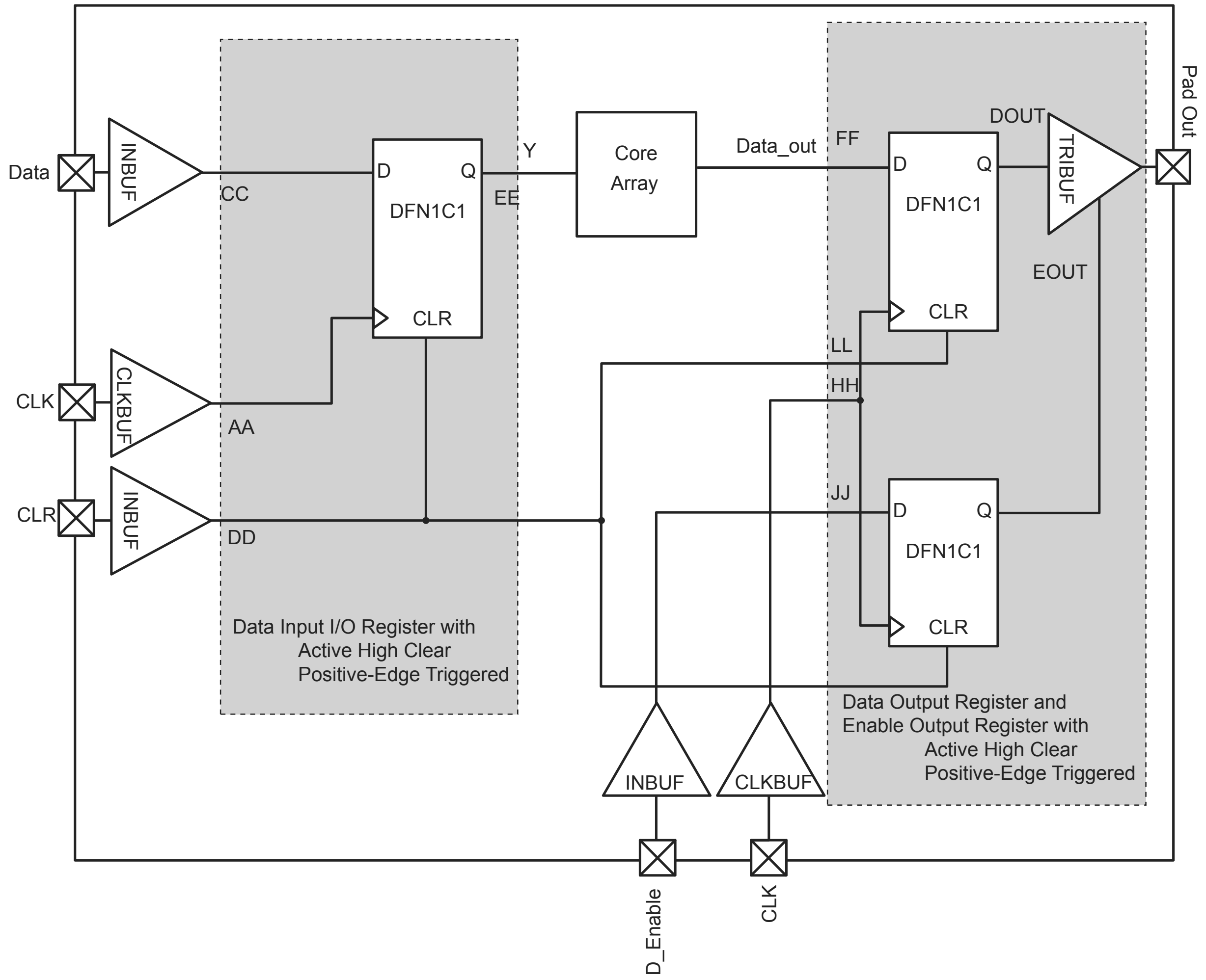


***Figure 2-13* • Timing Model of the Registered I/O Buffers with Asynchronous Clear**

Output Register

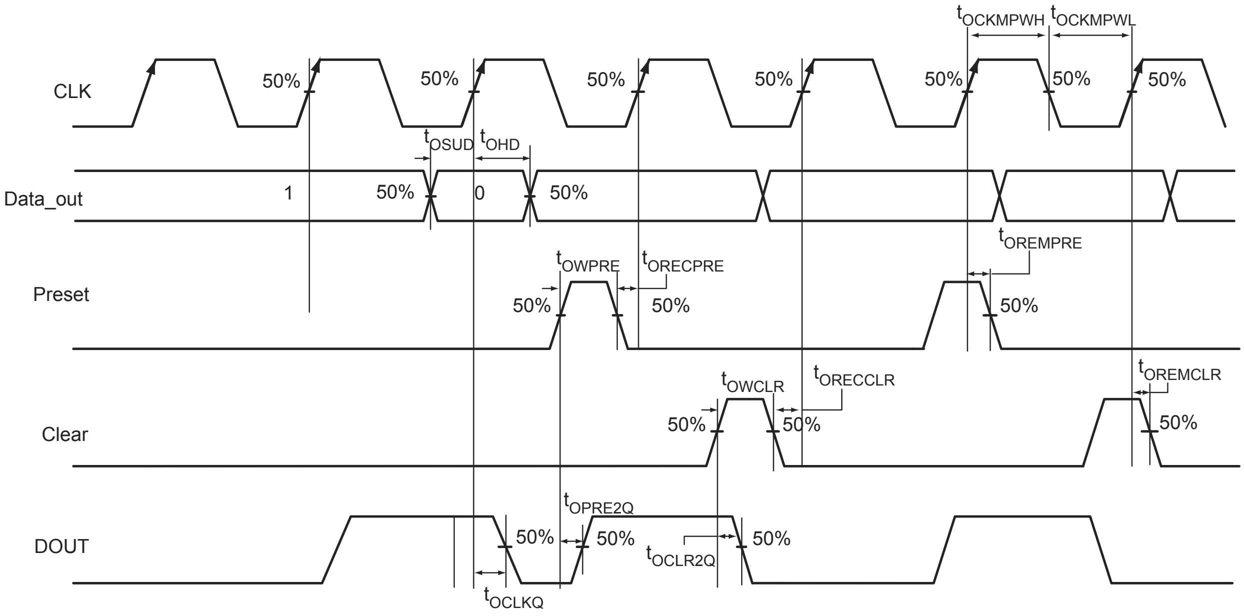


Figure 2-15 • **Output Register Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-74 • **Output Data Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	1.00	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.51	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	1.34	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	1.34	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.24	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.24	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.19	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.19	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width HIGH for the Output Data Register	0.31	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width LOW for the Output Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

DDR Module Specifications

Note: DDR is not supported for AGLN010, AGLN015, and AGLN020 devices.

Input DDR Module

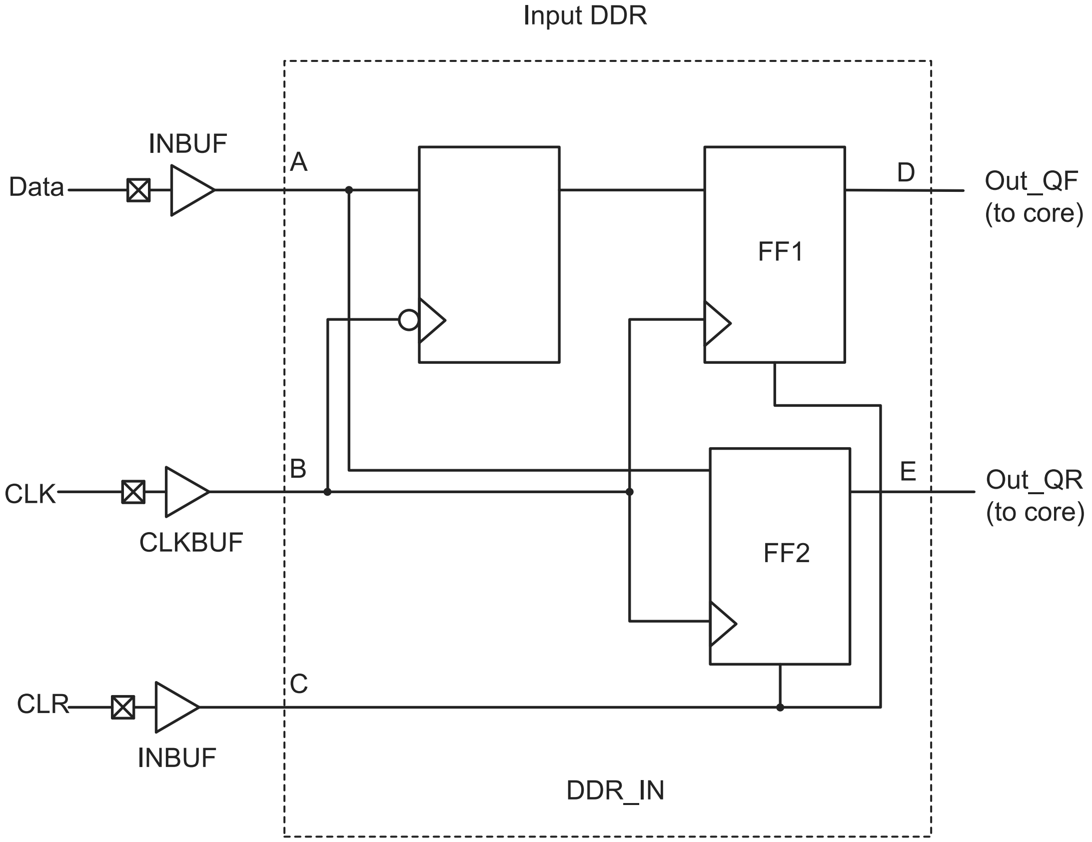


Figure 2-17 • **Input DDR Timing Model**

Table 2-78 • **Parameter Definitions**

Parameter Name	**Parameter Definition**	**Measuring Nodes (from, to)**
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR	B, D
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF	B, E
$t_{DDRISUD}$	Data Setup Time of DDR input	A, B
t_{DDRIHD}	Data Hold Time of DDR input	A, B
$t_{DDRICLR2Q1}$	Clear-to-Out Out_QR	C, D
$t_{DDRICLR2Q2}$	Clear-to-Out Out_QF	C, E
$t_{DDRIREMCLR}$	Clear Removal	C, B
$t_{DDRIRECCLR}$	Clear Recovery	C, B

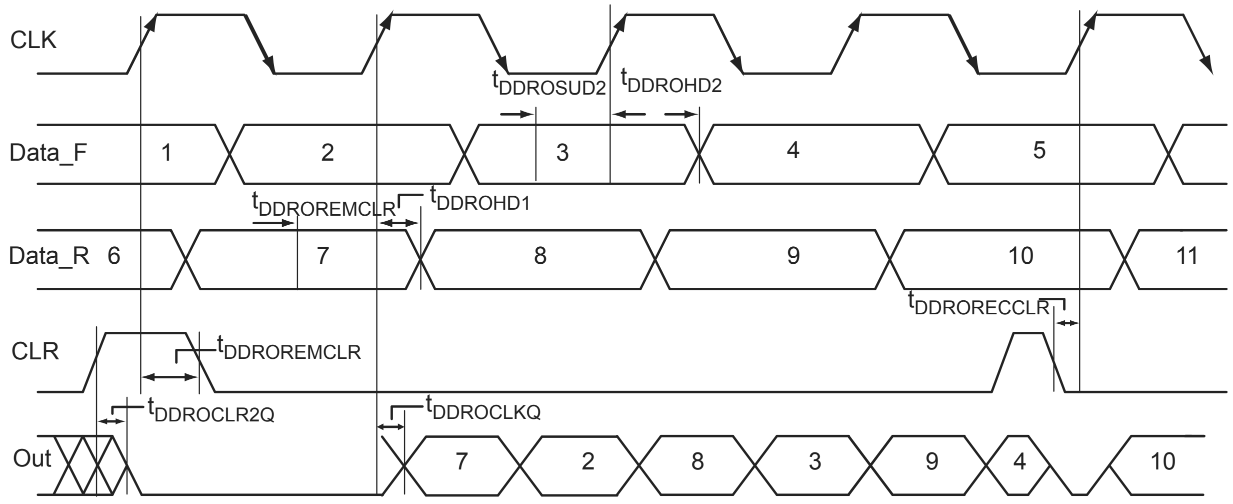


***Figure 2-20* • Output DDR Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

***Table 2-82* • Output DDR Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
$t_{DDROCLKQ}$	Clock-to-Out of DDR for Output DDR	1.07	ns
$t_{DDROSUD1}$	Data_F Data Setup for Output DDR	0.67	ns
$t_{DDROSUD2}$	Data_R Data Setup for Output DDR	0.67	ns
$t_{DDROHD1}$	Data_F Data Hold for Output DDR	0.00	ns
$t_{DDROHD2}$	Data_R Data Hold for Output DDR	0.00	ns
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out for Output DDR	1.38	ns
$t_{DDROREMCLR}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{DDRORECCLR}$	Asynchronous Clear Recovery Time for Output DDR	0.23	ns
$t_{DDROWCLR1}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.19	ns
$t_{DDROCKMPWH}$	Clock Minimum Pulse Width HIGH for the Output DDR	0.31	ns
$t_{DDROCKMPWL}$	Clock Minimum Pulse Width LOW for the Output DDR	0.28	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	250.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-92 • **AGLN125 Global Resource**
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.36	1.71	ns
t_{RCKH}	Input High Delay for Global Clock	1.39	1.82	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-93 • **AGLN250 Global Resource**
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.39	1.73	ns
t_{RCKH}	Input High Delay for Global Clock	1.41	1.84	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

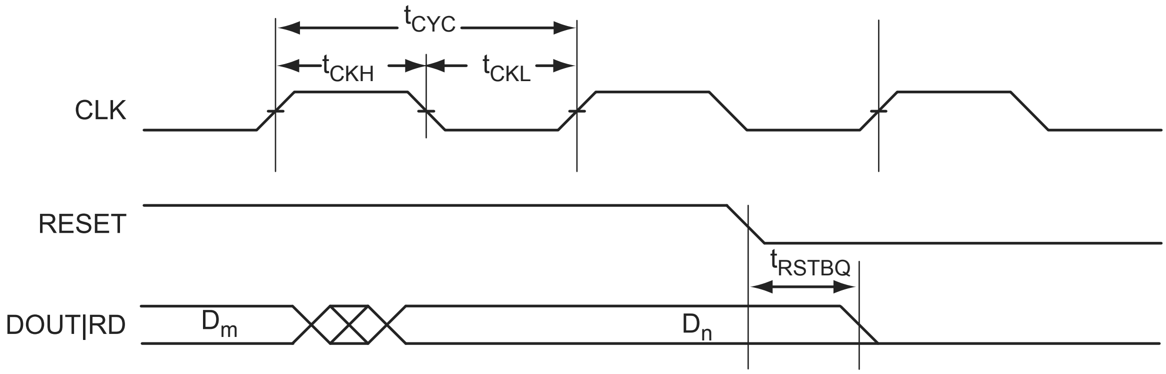


***Figure 2-32* • RAM Reset. Applicable to Both RAM4K9 and RAM512x18.**

Timing Characteristics

1.5 V DC Core Voltage

***Table 2-102* • RAM4K9**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.69	ns
t_{AH}	Address hold time	0.13	ns
t_{ENS}	REN, WEN setup time	0.68	ns
t_{ENH}	REN, WEN hold time	0.13	ns
t_{BKS}	BLK setup time	1.37	ns
t_{BKH}	BLK hold time	0.13	ns
t_{DS}	Input data (DIN) setup time	0.59	ns
t_{DH}	Input data (DIN) hold time	0.30	ns
t_{CKQ1}	Clock HIGH to new data valid on DOUT (output retained, WMODE = 0)	2.94	ns
	Clock HIGH to new data valid on DOUT (flow-through, WMODE = 1)	2.55	ns
t_{CKQ2}	Clock HIGH to new data valid on DOUT (pipelined)	1.51	ns
t_{C2CWWL}[1]	Address collision clk-to-clk delay for reliable write after write on same address; applicable to closing edge	0.23	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address; applicable to opening edge	0.35	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address; applicable to opening edge	0.41	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	1.72	ns
	RESET Low to data out Low on DOUT (pipelined)	1.72	ns
$t_{REMRSTB}$	RESET removal	0.51	ns
$t_{RECRSTB}$	RESET recovery	2.68	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. *For more information, refer to the application note AC374: Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based FPGAs and SoC FPGAs App Note.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

JTAG 1532 Characteristics

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the "User I/O Characteristics" section on page 2-15 for more details.

Timing Characteristics

1.5 V DC Core Voltage

***Table 2-110* • JTAG 1532**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{DISU}	Test Data Input Setup Time	1.00	ns
t_{DIHD}	Test Data Input Hold Time	2.00	ns
t_{TMSSU}	Test Mode Select Setup Time	1.00	ns
t_{TMDHD}	Test Mode Select Hold Time	2.00	ns
t_{TCK2Q}	Clock to Q (data out)	8.00	ns
t_{RSTB2Q}	Reset to Q (data out)	25.00	ns
F_{TCKMAX}	TCK Maximum Frequency	15	MHz
$t_{TRSTREM}$	ResetB Removal Time	0.58	ns
$t_{TRSTREC}$	ResetB Recovery Time	0.00	ns
$t_{TRSTMPW}$	ResetB Minimum Pulse	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

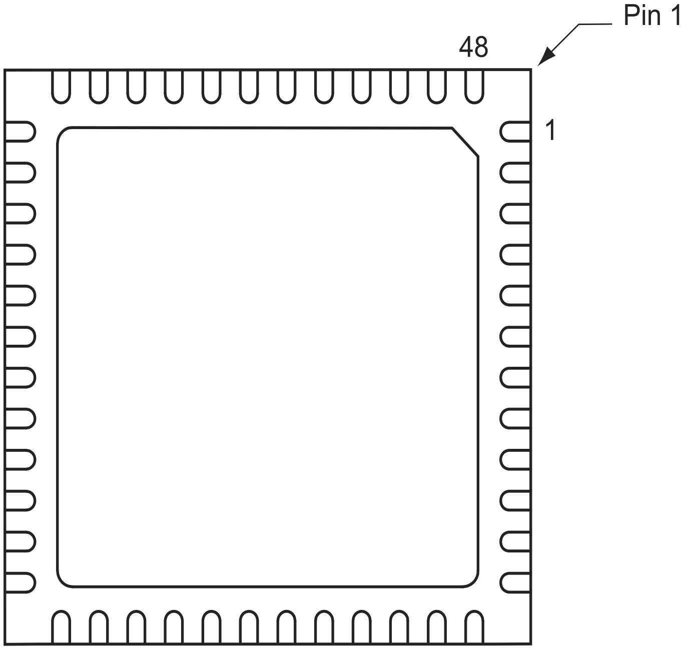
***Table 2-111* • JTAG 1532**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{DISU}	Test Data Input Setup Time	1.50	ns
t_{DIHD}	Test Data Input Hold Time	3.00	ns
t_{TMSSU}	Test Mode Select Setup Time	1.50	ns
t_{TMDHD}	Test Mode Select Hold Time	3.00	ns
t_{TCK2Q}	Clock to Q (data out)	11.00	ns
t_{RSTB2Q}	Reset to Q (data out)	30.00	ns
F_{TCKMAX}	TCK Maximum Frequency	9.00	MHz
$t_{TRSTREM}$	ResetB Removal Time	1.18	ns
$t_{TRSTREC}$	ResetB Recovery Time	0.00	ns
$t_{TRSTMPW}$	ResetB Minimum Pulse	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

UC36	
Pin Number	AGLN010 Function
A1	IO21RSB1
A2	IO18RSB1
A3	IO13RSB1
A4	GDC0/IO00RSB0
A5	IO06RSB0
A6	GDA0/IO04RSB0
B1	GEC0/IO37RSB1
B2	IO20RSB1
B3	IO15RSB1
B4	IO09RSB0
B5	IO08RSB0
B6	IO07RSB0
C1	IO22RSB1
C2	GEA0/IO34RSB1
C3	GND
C4	GND
C5	VCCIB0
C6	IO02RSB0
D1	IO33RSB1
D2	VCCIB1
D3	VCC
D4	VCC
D5	IO10RSB0
D6	IO11RSB0
E1	IO32RSB1
E2	FF/IO31RSB1
E3	TCK
E4	VPUMP
E5	TRST
E6	VJTAG
F1	IO29RSB1
F2	IO25RSB1
F3	IO23RSB1
F4	TDI
F5	TMS
F6	TDO

QN48



Notes:

1. *This is the bottom view of the package.*
2. *The die attach paddle of the package is tied to ground (GND).*

Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

VQ100	
Pin Number	AGLN125 Function
1	GND
2	GAA2/IO67RSB1
3	IO68RSB1
4	GAB2/IO69RSB1
5	IO132RSB1
6	GAC2/IO131RSB1
7	IO130RSB1
8	IO129RSB1
9	GND
10	GFB1/IO124RSB1
11	GFB0/IO123RSB1
12	VCOMPLF
13	GFA0/IO122RSB1
14	VCCPLF
15	GFA1/IO121RSB1
16	GFA2/IO120RSB1
17	VCC
18	VCCIB1
19	GEC0/IO111RSB1
20	GEB1/IO110RSB1
21	GEB0/IO109RSB1
22	GEA1/IO108RSB1
23	GEA0/IO107RSB1
24	VMV1
25	GNDQ
26	GEA2/IO106RSB1
27	FF/GEB2/IO105RSB1
28	GEC2/IO104RSB1
29	IO102RSB1
30	IO100RSB1
31	IO99RSB1
32	IO97RSB1
33	IO96RSB1
34	IO95RSB1
35	IO94RSB1
36	IO93RSB1
37	VCC
38	GND
39	VCCIB1
40	IO87RSB1
41	IO84RSB1
42	IO81RSB1
43	IO75RSB1
44	GDC2/IO72RSB1
45	GDB2/IO71RSB1
46	GDA2/IO70RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO65RSB0
58	GDC0/IO62RSB0
59	GDC1/IO61RSB0
60	GCC2/IO59RSB0
61	GCB2/IO58RSB0
62	GCA0/IO56RSB0
63	GCA1/IO55RSB0
64	GCC0/IO52RSB0
65	GCC1/IO51RSB0
66	VCCIB0
67	GND
68	VCC
69	IO47RSB0
70	GBC2/IO45RSB0
71	GBB2/IO43RSB0
72	IO42RSB0
73	GBA2/IO41RSB0
74	VMV0
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO32RSB0
83	IO28RSB0
84	IO25RSB0
85	IO22RSB0
86	IO19RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	IO09RSB0
94	IO07RSB0
95	GAC1/IO05RSB0
96	GAC0/IO04RSB0
97	GAB1/IO03RSB0
98	GAB0/IO02RSB0
99	GAA1/IO01RSB0
100	GAA0/IO00RSB0

VQ100	
Pin Number	**AGLN125Z Function**
1	GND
2	GAA2/IO67RSB1
3	IO68RSB1
4	GAB2/IO69RSB1
5	IO132RSB1
6	GAC2/IO131RSB1
7	IO130RSB1
8	IO129RSB1
9	GND
10	GFB1/IO124RSB1
11	GFB0/IO123RSB1
12	VCOMPLF
13	GFA0/IO122RSB1
14	VCCPLF
15	GFA1/IO121RSB1
16	GFA2/IO120RSB1
17	VCC
18	VCCIB1
19	GEC0/IO111RSB1
20	GEB1/IO110RSB1
21	GEB0/IO109RSB1
22	GEA1/IO108RSB1
23	GEA0/IO107RSB1
24	VMV1
25	GNDQ
26	GEA2/IO106RSB1
27	FF/GEB2/IO105RSB1
28	GEC2/IO104RSB1
29	IO102RSB1
30	IO100RSB1
31	IO99RSB1
32	IO97RSB1
33	IO96RSB1
34	IO95RSB1
35	IO94RSB1
36	IO93RSB1
37	VCC
38	GND
39	VCCIB1
40	IO87RSB1
41	IO84RSB1
42	IO81RSB1
43	IO75RSB1
44	GDC2/IO72RSB1
45	GDB2/IO71RSB1
46	GDA2/IO70RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO65RSB0
58	GDC0/IO62RSB0
59	GDC1/IO61RSB0
60	GCC2/IO59RSB0
61	GCB2/IO58RSB0
62	GCA0/IO56RSB0
63	GCA1/IO55RSB0
64	GCC0/IO52RSB0
65	GCC1/IO51RSB0
66	VCCIB0
67	GND
68	VCC
69	IO47RSB0
70	GBC2/IO45RSB0
71	GBB2/IO43RSB0
72	IO42RSB0
73	GBA2/IO41RSB0
74	VMV0
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO32RSB0
83	IO28RSB0
84	IO25RSB0
85	IO22RSB0
86	IO19RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	IO09RSB0
94	IO07RSB0
95	GAC1/IO05RSB0
96	GAC0/IO04RSB0
97	GAB1/IO03RSB0
98	GAB0/IO02RSB0
99	GAA1/IO01RSB0
100	GAA0/IO00RSB0

Revision	Changes	Page
Revision 10 (continued)	The following tables were updated with current available information. The equivalent software default drive strength option was added. Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings Table 2-28 • I/O Output Buffer Maximum Resistances [1] Table 2-29 • I/O Weak Pull-Up/Pull-Down Resistances Table 2-30 • I/O Short Currents IOSH/IOSL Timing tables in the "Single-Ended I/O Characteristics" section, including new tables for 3.3 V and 1.2 V LVCMOS wide range. Table 2-40 • Minimum and Maximum DC Input and Output Levels for LVCMOS 3.3 V Wide Range Table 2-63 • Minimum and Maximum DC Input and Output Levels Table 2-67 • Minimum and Maximum DC Input and Output Levels (new)	2-19 through 2-40
	The formulas in the notes to Table 2-29 • I/O Weak Pull-Up/Pull-Down Resistances were revised (SAR 21348).	2-24
	The text introducing Table 2-31 • Duration of Short Circuit Event before Failure was revised to state six months at 100° instead of three months at 110° for reliability concerns. The row for 110° was removed from the table.	2-25
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 24916): "It uses a 5-V tolerant input buffer and push-pull output buffer."	2-32
	The $F_{DDRIMAX}$ and F_{DDOMAX} values were added to tables in the "DDR Module Specifications" section (SAR 23919). A note was added stating that DDR is not supported for AGLN010, AGLN015, and AGLN020.	2-51
	Tables in the "Global Tree Timing Characteristics" section were updated with new information available.	2-64
	Table 2-100 • IGLOO nano CCC/PLL Specification and Table 2-101 • IGLOO nano CCC/PLL Specification were revised (SAR 79390).	2-70, 2-71
	Tables in the SRAM "Timing Characteristics" section and FIFO "Timing Characteristics" section were updated with new information available.	2-77, 2-85
	Table 3-3 • TRST and TCK Pull-Down Recommendations is new.	3-4
	A note was added to the "CS81" pin tables for AGLN060, AGLN060Z, AGLN125, AGLN125Z, AGLN250, and AGLN250Z indicating that pins F1 and F2 must be grounded (SAR 25007).	4-9, through 4-14
	A note was added to the "CS81" and "VQ100" pin tables for AGLN060 and AGLN060Z stating that bus hold is not available for pin H7 or pin 45 (SAR 24079).	4-9, 4-24
	The AGLN250 function for pin C8 in the "CS81" table was revised (SAR 22134).	4-13

Revision / Version	Changes	Page
Revision 1 (cont'd) Packaging Advance v0.2	The "QN48" pin diagram was revised.	4-16
	Note 2 for the "QN48", "QN68", and "100-Pin QFN" pin diagrams was changed to "The die attach paddle of the package is tied to ground (GND)."	4-16, 4-19
	The "VQ100" pin diagram was revised to move the pin IDs to the upper left corner instead of the upper right corner.	4-23
Revision 0 (Oct 2008) Product Brief Advance v0.2	The following tables and sections were updated to add the UC81 and CS81 packages for AGL030: "IGLOO nano Devices" "I/Os Per Package" "IGLOO nano Products Available in the Z Feature Grade" "Temperature Grade Offerings"	N/A
	The "I/Os Per Package" table was updated to add the following information to table note 4: "For nano devices, the VQ100 package is offered in both leaded and RoHS-compliant versions. All other packages are RoHS-compliant only."	II
	The "IGLOO nano Products Available in the Z Feature Grade" section was updated to remove QN100 for AGLN250.	VI
	The device architecture figures, Figure 1-3 • IGLOO Device Architecture Overview with Two I/O Banks (AGLN060, AGLN125) through Figure 1-4 • IGLOO Device Architecture Overview with Four I/O Banks (AGLN250), were revised. Figure 1-1 • IGLOO Device Architecture Overview with Two I/O Banks and No RAM (AGLN010 and AGLN030) is new.	1-4 through 1-5
	The "PLL and CCC" section was revised to include information about CCC-GLs in AGLN020 and smaller devices.	1-7
	The "I/Os with Advanced I/O Standards" section was revised to add information about IGLOO nano devices supporting double-data-rate applications.	1-8